

MM54HC688/MM74HC688 8-Bit Magnitude Comparator (Equality Detector)

General Description

This equality detector utilizes advanced silicon-gate CMOS technology to compare bit for bit two 8-bit words and indicates whether or not they are equal. The $\overline{P=Q}$ output indicates equality when it is low. A single active low enable is provided to facilitate cascading of several packages and enable comparison of words greater than 8 bits.

This device is useful in memory block decoding applications, where memory block enable signals must be generated from computer address information.

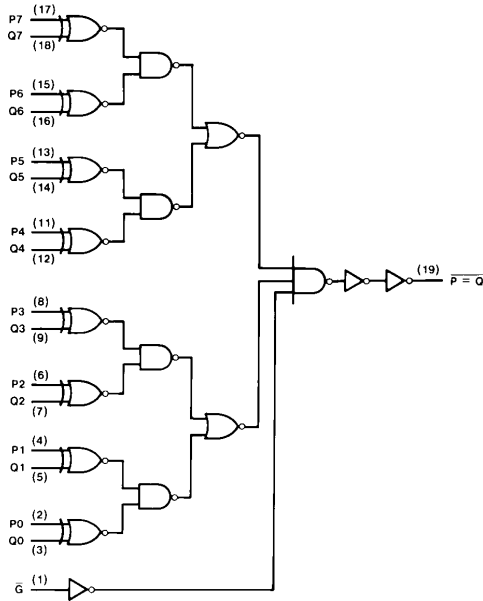
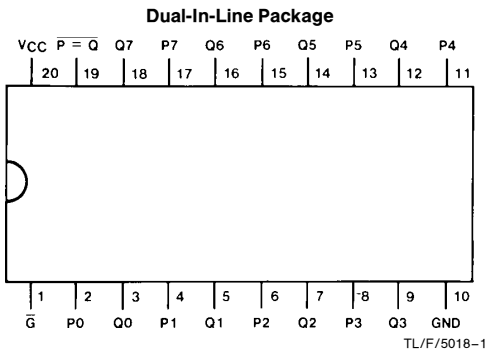
The comparator's output can drive 10 low power Schottky equivalent loads. This comparator is functionally and pin

compatible to the 54LS688/74LS688. All inputs are protected from damage due to static discharge by diodes to V_{CC} and ground.

Features

- Typical propagation delay: 20 ns
- Wide power supply range: 2–6V
- Low quiescent current: 80 μ A (74 Series)
- Large output current: 4 mA (74 Series)
- Same as 'HC521

Connection and Logic Diagrams



Truth Table

Inputs		$\overline{P=Q}$
Data P,Q	Enable \overline{G}	
P = Q	L	L
P > Q	L	H
P < Q	L	H
X	H	H

MM54HC688/MM74HC688 8-Bit Magnitude Comparator (Equality Detector)

Absolute Maximum Ratings (Notes 1 and 2)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/Distributors for availability and specifications.

Supply Voltage (V_{CC})	-0.5 to +7.0V
DC Input Voltage (V_{IN})	-1.5 to $V_{CC} + 1.5V$
DC Output Voltage (V_{OUT})	-0.5 to $V_{CC} + 0.5V$
Clamp Diode Current (I_{IK}, I_{OK})	± 20 mA
DC Output Current, per pin (I_{OUT})	± 25 mA
DC V_{CC} or GND Current, per pin (I_{CC})	± 50 mA
Storage Temperature Range (T_{STG})	-65°C to +150°C
Power Dissipation (P_D) (Note 3)	600 mW
S.O. Package only	500 mW
Lead Temp. (T_L) (Soldering 10 seconds)	260°C

Operating Conditions

	Min	Max	Units
Supply Voltage (V_{CC})	2	6	V
DC Input or Output Voltage (V_{IN}, V_{OUT})	0	V_{CC}	V
Operating Temp. Range (T_A)			
MM74HC	-40	+85	°C
MM54HC	-55	+125	°C
Input Rise or Fall Times (t_r, t_f)			
$V_{CC} = 2.0V$		1000	ns
$V_{CC} = 4.5V$		500	ns
$V_{CC} = 6.0V$		400	ns

DC Electrical Characteristics (Note 4)

Symbol	Parameter	Conditions	V_{CC}	$T_A = 25^\circ C$			Units	
				74HC		54HC		
				$T_A = -40$ to $85^\circ C$		$T_A = -55$ to $125^\circ C$		
				Typ	Guaranteed Limits			
V_{IH}	Minimum High Level Input Voltage		2.0V		1.5	1.5	1.5	V
			4.5V		3.15	3.15	3.15	V
			6.0V		4.2	4.2	4.2	V
V_{IL}	Maximum Low Level Input Voltage**		2.0V		0.5	0.5	0.5	V
			4.5V		1.35	1.35	1.35	V
			6.0V		1.8	1.8	1.8	V
V_{OH}	Minimum High Level Output Voltage	$V_{IN} = V_{IH}$ or V_{IL} $ I_{OUT} \leq 20 \mu A$	2.0V	2.0	1.9	1.9	1.9	V
			4.5V	4.5	4.4	4.4	4.4	V
			6.0V	6.0	5.9	5.9	5.9	V
		$V_{IN} = V_{IH}$ or V_{IL} $ I_{OUT} \leq 4.0$ mA $ I_{OUT} \leq 5.2$ mA	4.5V	4.2	3.98	3.84	3.7	V
			6.0V	5.7	5.48	5.34	5.2	V
V_{OL}	Maximum Low Level Output Voltage	$V_{IN} = V_{IH}$ or V_{IL} $ I_{OUT} \leq 20 \mu A$	2.0V	0	0.1	0.1	0.1	V
			4.5V	0	0.1	0.1	0.1	V
			6.0V	0	0.1	0.1	0.1	V
		$V_{IN} = V_{IH}$ or V_{IL} $ I_{OUT} \leq 4.0$ mA $ I_{OUT} \leq 5.2$ mA	4.5V	0.2	0.26	0.33	0.4	V
			6.0V	0.2	0.26	0.33	0.4	V
I_{IN}	Maximum Input Current	$V_{IN} = V_{CC}$ or GND	6.0V		± 0.1	± 1.0	± 1.0	μA
I_{CC}	Maximum Quiescent Supply Current	$V_{IN} = V_{CC}$ or GND $I_{OUT} = 0 \mu A$	6.0V		8.0	80	160	μA

Note 1: Absolute Maximum Ratings are those values beyond which damage to the device may occur.

Note 2: Unless otherwise specified all voltages are referenced to ground.

Note 3: Power Dissipation temperature derating — plastic "N" package: -12 mW/°C from 65°C to 85°C; ceramic "J" package: -12 mW/°C from 100°C to 125°C.

Note 4: For a power supply of $5V \pm 10\%$ the worst case output voltages (V_{OH} and V_{OL}) occur for HC at 4.5V. Thus the 4.5V values should be used when designing with this supply. Worst case V_{IH} and V_{IL} occur at $V_{CC} = 5.5V$ and 4.5V respectively. (The V_{IH} value at 5.5V is 3.85V.) The worst case leakage current (I_{IN} , I_{CC} , and I_{OZ}) occur for CMOS at the higher voltage and so the 6.0V values should be used.

** V_{IL} limits are currently tested at 20% of V_{CC} . The above V_{IL} specification (30% of V_{CC}) will be implemented no later than Q1, CY'89.

AC Electrical Characteristics

$V_{CC}=5V$, $T_A=25^\circ C$, $C_L=15\text{ pF}$, $t_r=t_f=6\text{ ns}$

Symbol	Parameter	Conditions	Typ	Guaranteed Limit	Units
t_{PHL} , t_{PLH}	Maximum Propagation Delay, any P or Q to Output		21	30	ns
t_{PLH} , t_{PHL}	Maximum Propagation Delay, Enable to any Output		14	20	ns

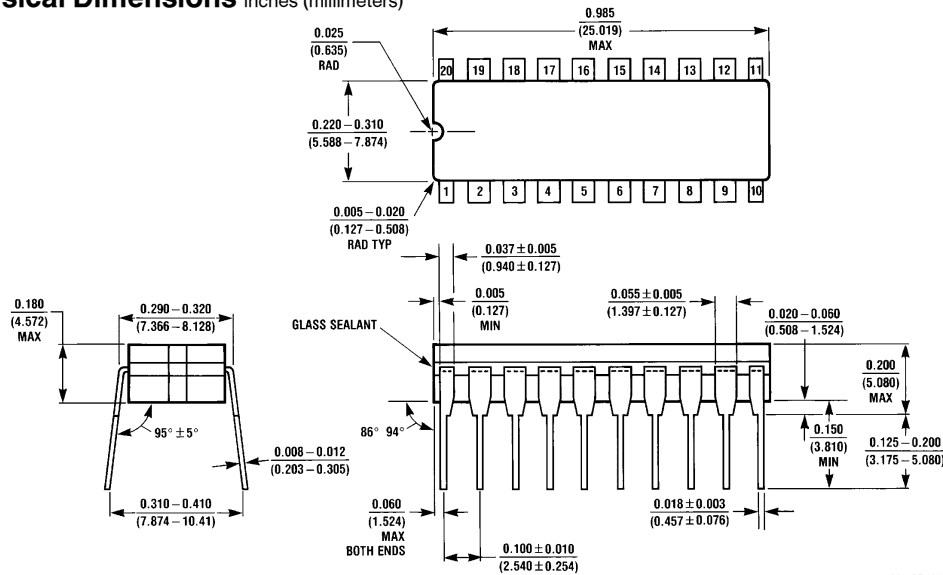
AC Electrical Characteristics

$V_{CC}=2.0V$ to $6.0V$, $C_L=50\text{ pF}$, $t_r=t_f=6\text{ ns}$ (unless otherwise specified)

Symbol	Parameter	Conditions	V_{CC}	$T_A=25^\circ C$		74HC	54HC	Units
						$T_A=-40\text{ to }85^\circ C$	$T_A=-55\text{ to }125^\circ C$	
				Typ	Guaranteed Limits			
t_{PHL} , t_{PLH}	Maximum Propagation Delay, P or Q to Output		2.0V	60	175	220	263	ns
			4.5V	22	35	44	53	ns
			6.0V	19	30	38	45	ns
t_{PHL} , t_{PLH}	Maximum Propagation Delay, Enable to Output		2.0V	45	120	150	180	ns
			4.5V	15	24	30	36	ns
			6.0V	13	20	25	30	ns
t_{THL} , t_{TLH}	Maximum Output Rise and Fall Time		2.0V	30	75	95	110	ns
			4.5V	8	15	19	22	ns
			6.0V	7	13	16	19	ns
C_{PD}	Power Dissipation Capacitance (Note 5)			45				pF
C_{IN}	Maximum Input Capacitance			5	10	10	10	pF

Note 5: C_{PD} determines the no load dynamic power consumption, $P_D=C_{PD} V_{CC}^2 f+I_{CC} V_{CC}$, and the no load dynamic current consumption, $I_S=C_{PD} V_{CC} f+I_{CC}$.

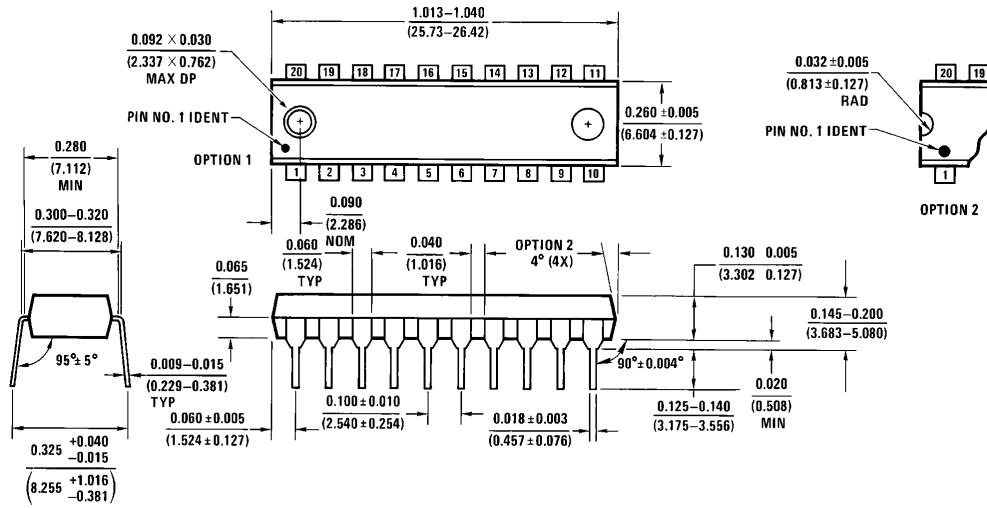
Physical Dimensions inches (millimeters)



Order Number MM54HC688J or MM74HC688J
NS Package Number J20A

J20A (REV M)

Physical Dimensions inches (millimeters) (Continued)



Order Number MM74HC688N
NS Package Number N20A

N20A (REV G)

LIFE SUPPORT POLICY

NATIONAL'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF THE PRESIDENT OF NATIONAL SEMICONDUCTOR CORPORATION. As used herein:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, and whose failure to perform, when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury to the user.
2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.



National Semiconductor Corporation
1111 West Bardin Road
Arlington, TX 76017
Tel: 1(800) 272-9959
Fax: 1(800) 737-7018

National Semiconductor Europe
Fax: (+49) 0-180-530 85 86
Email: cnjwge@tevm2.nsc.com
Deutsch Tel: (+49) 0-180-530 85 85
English Tel: (+49) 0-180-532 78 32
Français Tel: (+49) 0-180-532 93 58
Italiano Tel: (+49) 0-180-534 16 80

National Semiconductor Hong Kong Ltd.
19th Floor, Straight Block,
Ocean Centre, 5 Canton Rd.
Tsimshatsui, Kowloon
Hong Kong
Tel: (852) 2737-1600
Fax: (852) 2736-9960

National Semiconductor Japan Ltd.
Tel: 81-043-299-2309
Fax: 81-043-299-2408

National does not assume any responsibility for use of any circuitry described, no circuit patent licenses are implied and National reserves the right at any time without notice to change said circuitry and specifications.